



SEMITRANS® 2

Fast IGBT4 Modules

SKM100GAL12T4

Features

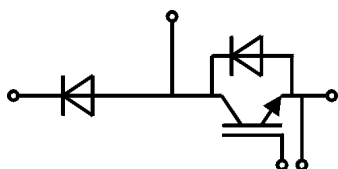
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_{Cnom}$
- Fast & soft inverse CAL diodes
- Large clearance (10 mm) and creepage distances (20 mm)
- Isolated copper baseplate using DBC Technology (Direct Copper Bonding)
- UL recognized, file no. E63532

Typical Applications*

- DC/DC – converter
- Brake chopper
- Switched reluctance motor
- DC – motor

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm.
 $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j = 150^\circ$



GAL

Absolute Maximum Ratings

Symbol	Conditions	Values	Unit
IGBT			
V_{CES}	$T_j = 25^\circ\text{C}$	1200	V
I_C	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	160
		$T_c = 80^\circ\text{C}$	123
I_{Cnom}		100	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$	300	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 150^\circ\text{C}$	10
T_j		-40 ... 175	$^\circ\text{C}$
Inverse diode			
I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	121
		$T_c = 80^\circ\text{C}$	91
I_{Fnom}		100	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$	300	A
I_{FSM}	$t_p = 10\text{ ms}$, sin 180° , $T_j = 25^\circ\text{C}$	550	A
T_j		-40 ... 175	$^\circ\text{C}$
Freewheeling diode			
I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	121
		$T_c = 80^\circ\text{C}$	91
I_{Fnom}		100	A
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I_{FSM}	$t_p = 10\text{ ms}$, sin 180° , $T_j = 25^\circ\text{C}$	550	A
T_j		-40 ... 175	$^\circ\text{C}$
Module			
$I_{t(RMS)}$	$T_{terminal} = T_{terminal} < 80^\circ\text{C}$	200	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50Hz, $t = 1\text{ min}$	4000	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 100\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.8	2.05	V
		$T_j = 150^\circ\text{C}$	2.2	2.4	V
V_{CE0}		$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	10.0	11.5	m Ω
		$T_j = 150^\circ\text{C}$	15.0	16.0	m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 3.8\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
		$T_j = 150^\circ\text{C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$	$f = 1\text{ MHz}$	6.15		nF
C_{oes}	$V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	0.40		nF
C_{res}		$f = 1\text{ MHz}$	0.345		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		565		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		7.5		Ω



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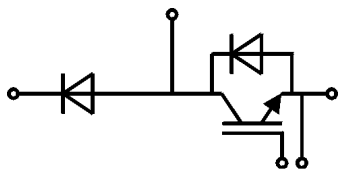
Typical Applications*

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Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm.
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
t _{d(on)}	V _{CC} = 600 V	T _j = 150 °C		165		ns
t _r	I _C = 100 A	T _j = 150 °C		47		ns
E _{on}	V _{GE} = ±15 V	T _j = 150 °C		15		mJ
t _{d(off)}	R _{G on} = 1 Ω	T _j = 150 °C		400		ns
t _f	R _{G off} = 1 Ω	T _j = 150 °C		75		ns
E _{off}	di/dt _{on} = 1800 A/μs	T _j = 150 °C		10.2		mJ
	di/dt _{off} = 1130 A/μs	T _j = 150 °C				
R _{th(j-c)}	per IGBT				0.27	K/W
Inverse diode						
V _F = V _{EC}	I _F = 100 A	T _j = 25 °C		2.20	2.52	V
	V _{GE} = 0 V chip	T _j = 150 °C		2.15	2.47	V
V _{F0}		T _j = 25 °C		1.3	1.5	V
		T _j = 150 °C		0.9	1.1	V
r _F		T _j = 25 °C		9.0	10.2	mΩ
		T _j = 150 °C		12.5	13.7	mΩ
I _{RRM}	I _F = 100 A	T _j = 150 °C		54		A
Q _{rr}	di/dt _{off} = 1600 A/μs	T _j = 150 °C		15.7		μC
E _{rr}	V _{GE} = ±15 V V _{CC} = 600 V	T _j = 150 °C		5.9		mJ
R _{th(j-c)}	per diode				0.48	K/W
Freewheeling diode						
V _F = V _{EC}	I _F = 100 A	T _j = 25 °C		2.20	2.52	V
	V _{GE} = 0 V chip	T _j = 150 °C		2.15	2.47	V
V _{F0}		T _j = 25 °C		1.3	1.5	V
		T _j = 150 °C		0.9	1.1	V
r _F		T _j = 25 °C		9.0	10.2	mΩ
		T _j = 150 °C		12.5	13.7	mΩ
I _{RRM}	I _F = 100 A	T _j = 150 °C		165		A
Q _{rr}	di/dt _{off} = 1600 A/μs	T _j = 150 °C		15.7		μC
E _{rr}	V _{GE} = ±15 V V _{CC} = 600 V	T _j = 150 °C		5.9		mJ
R _{th(j-c)}	per Diode				0.48	K/W
Module						
L _{CE}					30	nH
R _{CC'+EE'}	terminal-chip	T _C = 25 °C		0.65		mΩ
		T _C = 125 °C		1		mΩ
R _{th(c-s)}	per module			0.04	0.05	K/W
M _s	to heat sink M6		3		5	Nm
M _t		to terminals M5	2.5		5	Nm
						Nm
w					160	g



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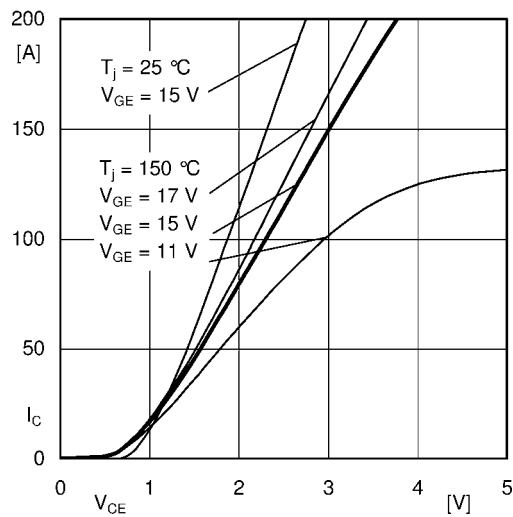


Fig. 1: Typ. output characteristic, inclusive $R_{CC'} + EE'$

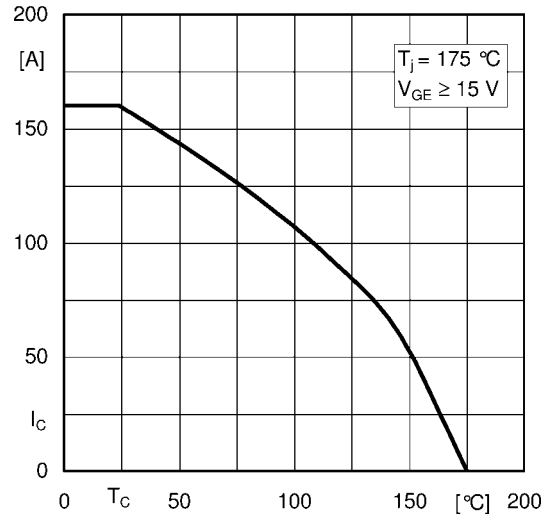


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

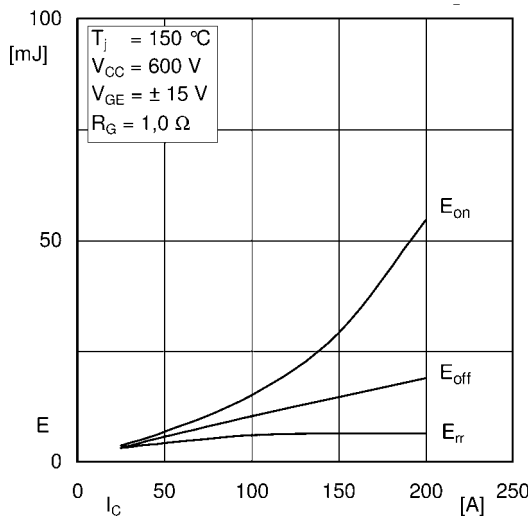


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

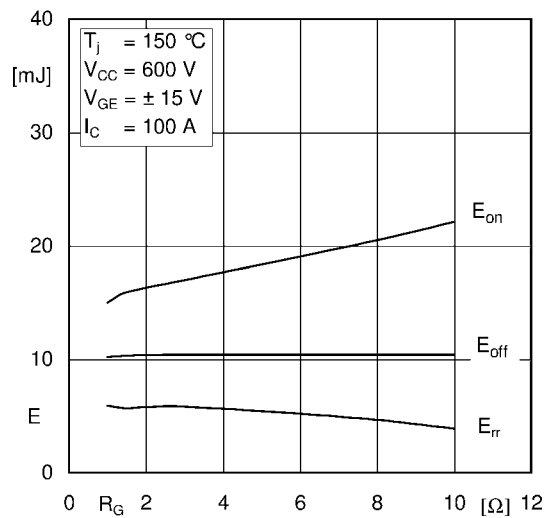


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

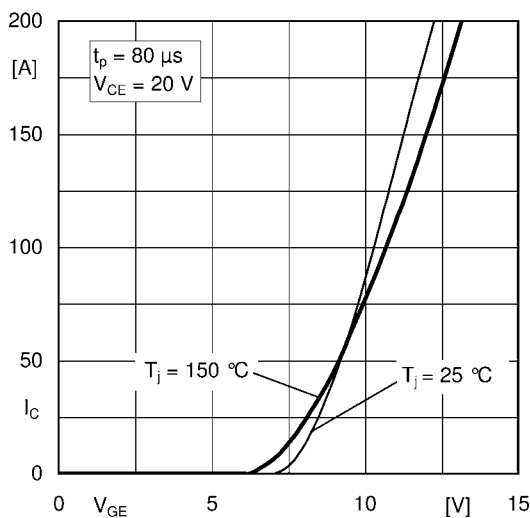


Fig. 5: Typ. transfer characteristic

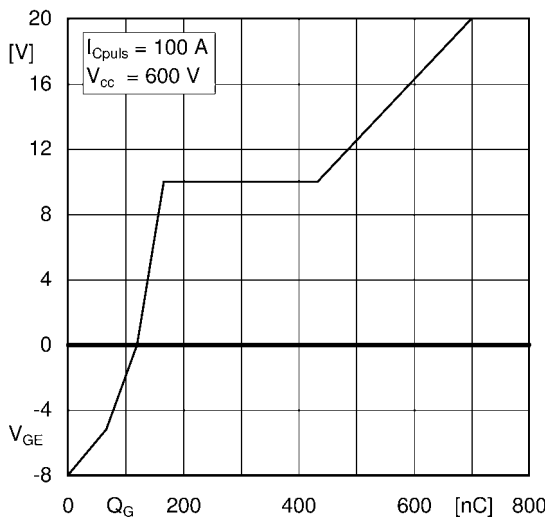
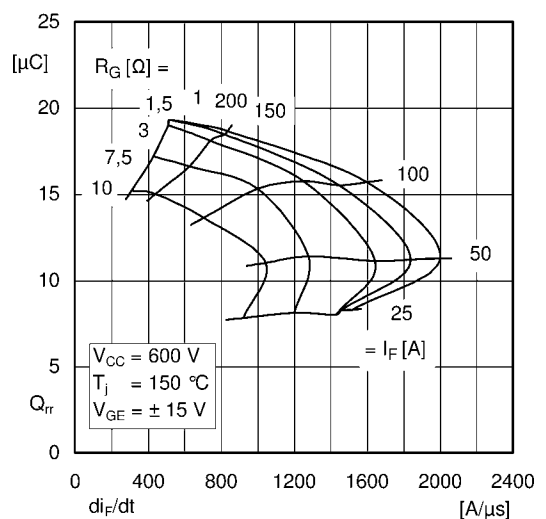
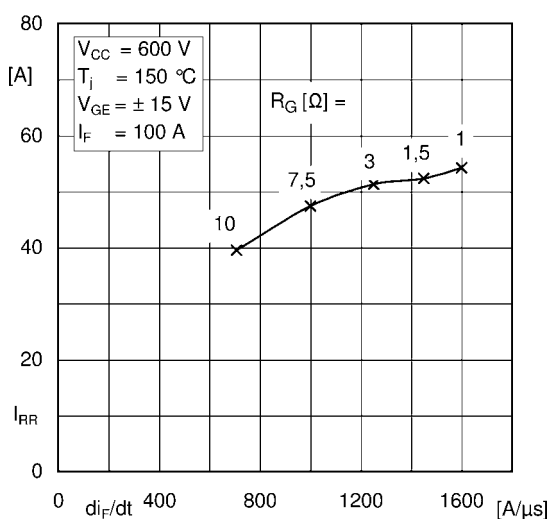
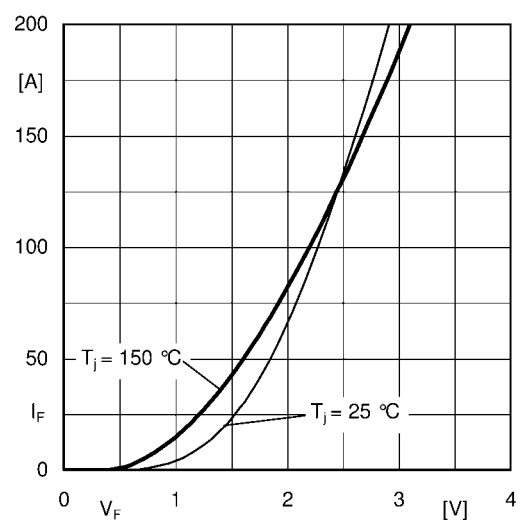
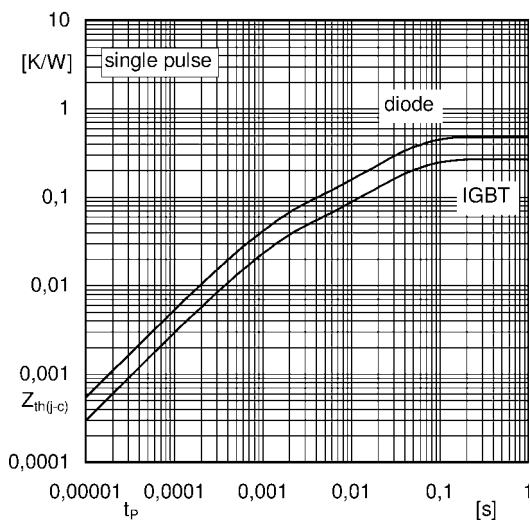
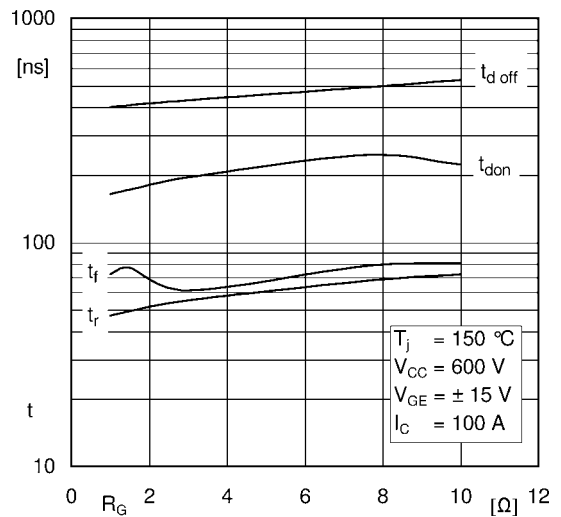
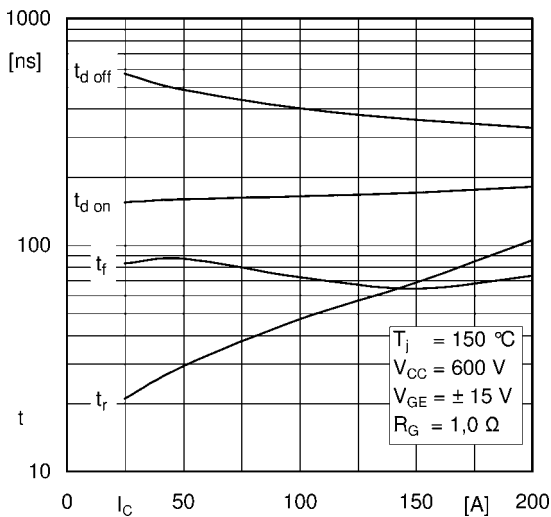
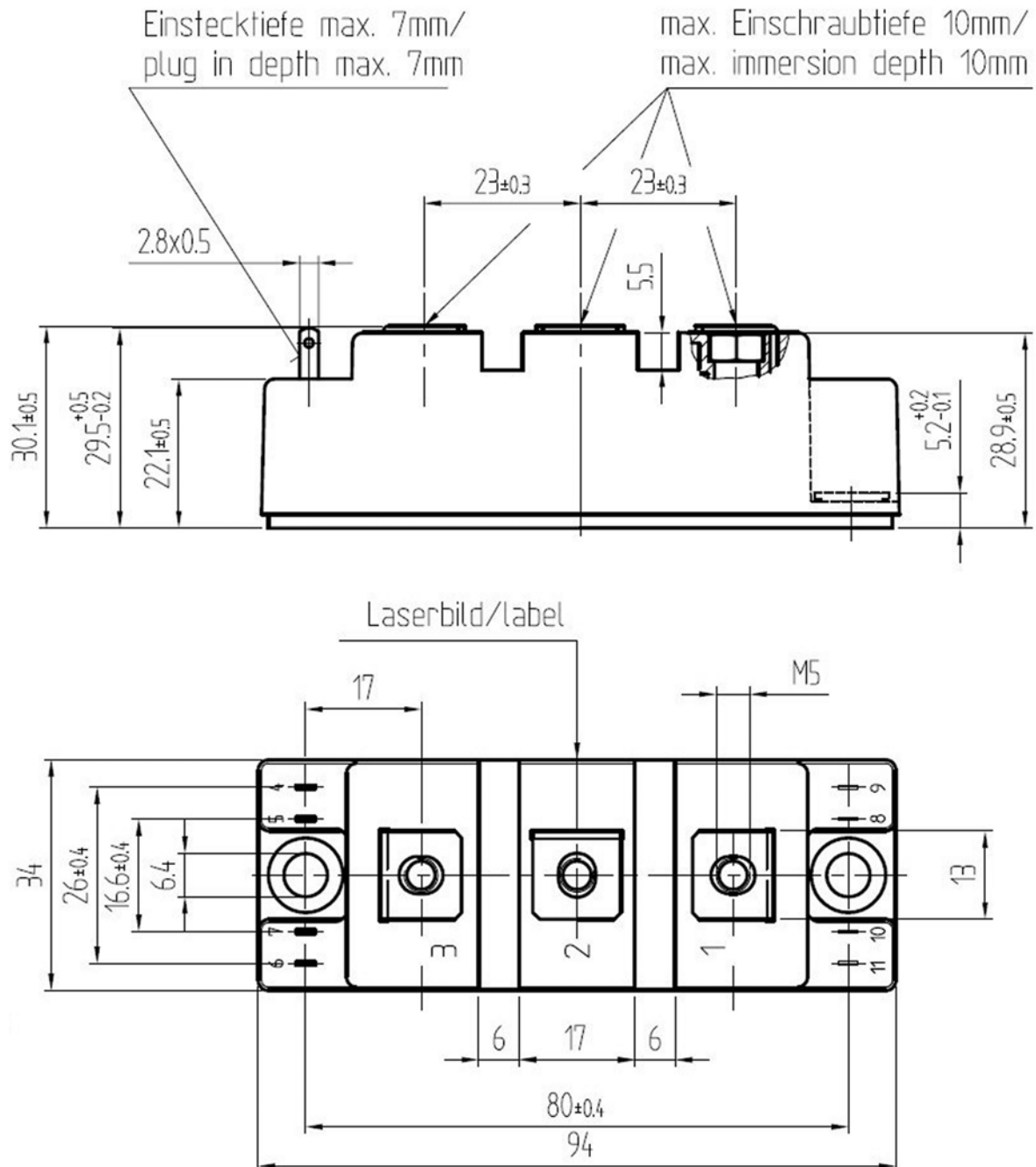
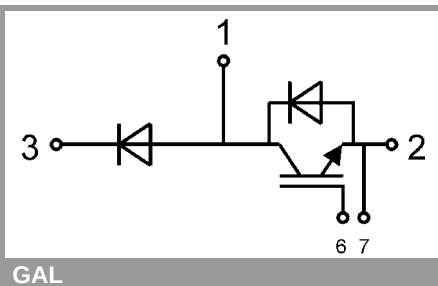


Fig. 6: Typ. gate charge characteristic





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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.